



Preliminary data

HiPerFAST™ IGBT with Diode Combi Pack

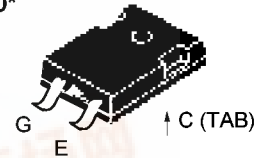
IXGH20N60BU1 IXGH20N60BU1S

$V_{CES} = 600 \text{ V}$
 $I_{C(25)} = 40 \text{ A}$
 $V_{CE(sat)typ} = 1.7 \text{ V}$
 $t_{fi(typ)} = 100 \text{ ns}$

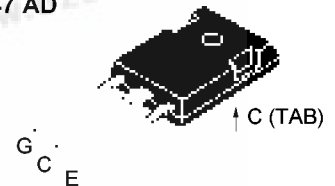


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	40	A
I_{C90}	$T_C = 90^\circ\text{C}$	20	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	80	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 40$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	150	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque, TO-247 AD	1.13/10	Nm/lb.in.
Weight	TO-247 SMD	4	g
	TO-247 AD	6	g

TO-247 SMD*



TO-247 AD



G = Gate, C = Collector,
E = Emitter, TAB = Collector

*Add suffix letter "S" for surface mountable package

Features

- International standard packages
JEDEC TO-247 SMD surface mountable and JEDEC TO-247 AD
- High frequency IGBT and antiparallel FRED in one package
- High current handling capability
- HiPerFAST™ HDMOS™ process
- MOS Gate turn-on
- drive simplicity

Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

Advantages

- Space savings (two devices in one package)
- High power density
- Suitable for surface mounting
- Very low switching losses for high frequency applications
- Easy to mount with 1 screw, TO-247 (insulated mounting screw hole)

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			200 μA 8 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$	1.7	2.0	V

IXYS

IXGH20N60BU1

IXGH20N60BU1S

Symbol Test Conditions

Characteristic Values

(T_J = 25°C, unless otherwise specified)

		min.	typ.	max.
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	9	17	S
C_{ies} C_{oes} C_{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1500 175 40	pF pF pF
Q_g Q_{ge} Q_{gc}	I _C = I _{C90} ; V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		90 11 30	nC nC nC
t_{d(on)} t_{ri} E_{on} t_{d(off)} t_{fi} E_{off}	Inductive load, T_J = 25°C I _C = I _{C90} ; V _{GE} = 15 V, L = 100 μH, V _{CE} = 0.8 V _{CES} ; R _G = R _{off} = 10 Ω Note 1		15 35 0.15 150 100 0.7	ns ns mJ ns ns mJ
t_{d(on)} t_{ri} E_{on} t_{d(off)} t_{fi} E_{off}	Inductive load, T_J = 125°C I _C = I _{C90} ; V _{GE} = 15 V, L = 100 μH V _{CE} = 0.8 V _{CES} ; R _G = R _{off} = 10 Ω Note 1		15 35 0.15 220 140 1.2	ns ns mJ ns ns mJ
R_{thJC} R_{thCK}			0.25	0.83 K/W K/W

Reverse Diode (FRED)

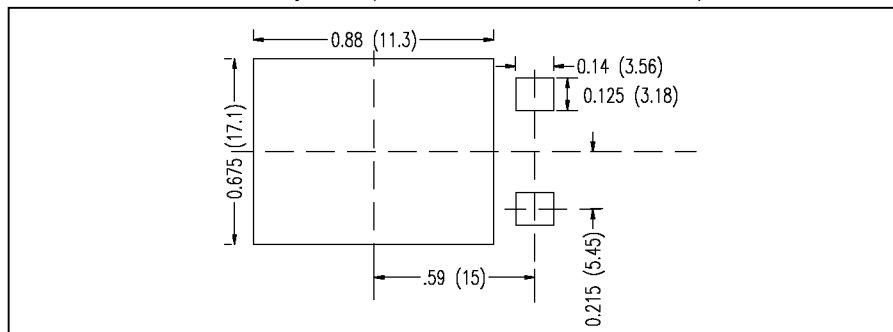
Characteristic Values

(T_J = 25°C, unless otherwise specified)

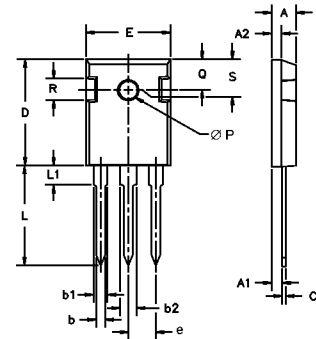
Symbol	Test Conditions	min.	typ.	max.
V_F	I _F = I _{C90} ; V _{GE} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.6 V
I_{RM} t_{rr}	I _F = I _{C90} ; V _{GE} = 0 V, -di _F /dt = 240 A/μs V _R = 360 V I _F = 1 A; -di _F /dt = 100 A/μs; V _R = 30 V		10 150 35	15 A ns ns
R_{thJC}				1 K/W

Note 1: Switching times may increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G

Min. Recommended Footprint (Dimensions in inches and mm)

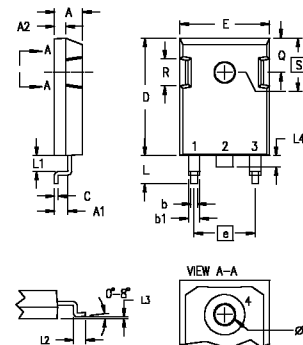


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-247 SMD Outline



1. Gate
2. Collector
3. Emitter
4. Collector

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45	BSC	.215	BSC
L	4.90	5.10	.193	.201
L1	2.70	2.90	.106	.114
L2	2.10	2.30	.083	.091
L3	0.00	0.10	.00	.004
L4	1.90	2.10	.075	.083
ØP	3.55	3.65	.140	.144
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	6.15	BSC	.242	BSC



limits, test conditions, and dimensions.

by one or more of the following U.S. patents: 4,835,592; 4,881,106; 5,017,508; 5,049,961; 5,187,117; 5,486,715